N-Channel 70-V (D-S) MOSFET

Key Features:

- Low r_{DS(on)} trench technology
- · Low thermal impedance
- · Fast switching speed

Typical Applications:

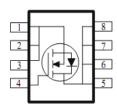
- DC/DC Conversion Circuits
- Motor Drives

PRODUCT SUMMARY			
V _{DS} (V)	$r_{DS(on)}(m\Omega)$	I⊳(A)	
70	6 @ V _{GS} = 10V	80°	
70	$7 @ V_{GS} = 4.5V$	60	









ABSOLUTE MAXIMUM RATINGS ($T_A = 25^{\circ}$ C UNLESS OTHERWISE NOTED)							
Parameter	Symbol	Limit	Units				
Drain-Source Voltage			70	V			
Gate-Source Voltage	V_{GS}	±20	V				
	T _C =25°C		80 ^c	A			
Continuous Drain Current	T _C =70°C	I _D	80 ^c				
Continuous Diam Guilent	T _A =25°C		24 ^a				
	T _A =70°C		19 ^a				
Pulsed Drain Current ^b			100				
Continuous Source Current (Diode Conduction) a		I _S	7.3				
	T _C =25°C		100	W			
Power Dissipation	T _C =70°C	P_D	65				
r ower dissipation	T _A =25°C] ' b	5 ^a				
	T _A =70°C		3.2 ^a				
Operating Junction and Storage Temperature Range		T_J,T_stg	-55 to 150	°C			

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Ambient ^a	t <= 10 sec	$R_{\theta JA}$	25	°C/W			
IMAXIIIIUIII SUIICUOII-to-AIIISIEIIt	Steady State	IXOJA	65				
Maximum Junction-to-Case	Steady State	$R_{\theta JC}$	1.2				

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature
- c. Package limited

Electrical Characteristics

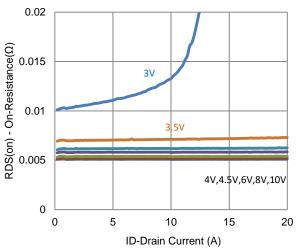
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250 \text{ uA}$	1			V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			±100	nA	
Zara Cata Valtara Brain Current		$V_{DS} = 56 \text{ V}, V_{GS} = 0 \text{ V}$			1 uA		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 56 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			10	uA	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	40			Α	
Dania Commo On Bosistano a	r	$V_{GS} = 10 \text{ V}, I_{D} = 12 \text{ A}$	6		6		
Drain-Source On-Resistance ^a	r _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$			7	mΩ	
Forward Transconductance a	g_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 12 \text{ A}$		92		S	
Diode Forward Voltage ^a	V_{SD}	$I_{S} = 3.7 \text{ A}, V_{GS} = 0 \text{ V}$		0.71		V	
		Dynamic ^b					
Total Gate Charge	Q_g	$V_{DS} = 35 \text{ V}, V_{GS} = 4.5 \text{ V},$		61			
Gate-Source Charge	Q_{gs}	$V_{DS} = 33 \text{ V}, V_{GS} = 4.3 \text{ V},$ $I_{D} = 12 \text{ A}$		22		nC	
Gate-Drain Charge	Q_gd	1D = 12 A		18			
Turn-On Delay Time	t _{d(on)}	$V_{DS} = 35 \text{ V}, R_{L} = 2.9 \Omega,$		30			
Rise Time	t _r	$V_{DS} = 33 \text{ V}, N_L - 2.9 \Omega,$ $I_D = 12 \text{ A},$		23		no	
Turn-Off Delay Time	$t_{d(off)}$	$V_{GEN} = 10 \text{ V}, R_{GEN} = 6 \Omega$		183		ns	
Fall Time	t _f	V GEN = 10 V, 1 (GEN = 0.12		53			
Input Capacitance	C _{iss}			7271			
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ Mhz}$		478		pF	
Reverse Transfer Capacitance	C _{rss}			423			

Notes

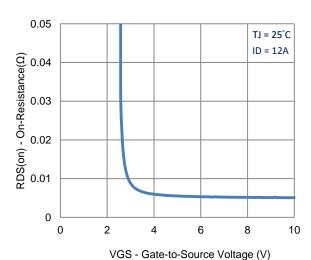
- Pulse test: PW <= 300us duty cycle <= 2%.
- Guaranteed by design, not subject to production testing.

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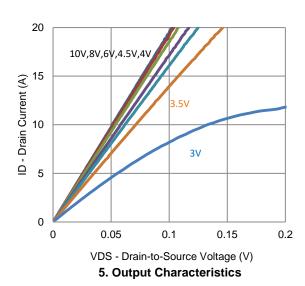
Typical Electrical Characteristics

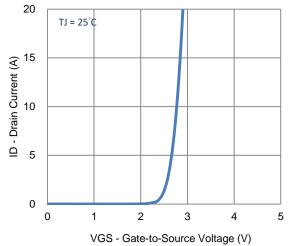


1. On-Resistance vs. Drain Current

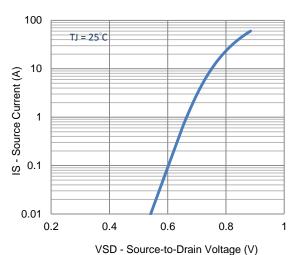


3. On-Resistance vs. Gate-to-Source Voltage

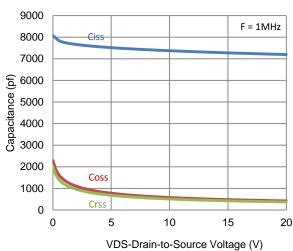




2. Transfer Characteristics

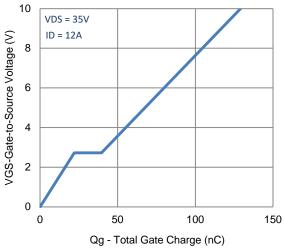


4. Drain-to-Source Forward Voltage

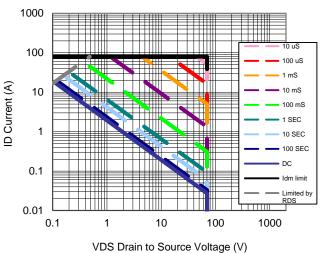


6. Capacitance

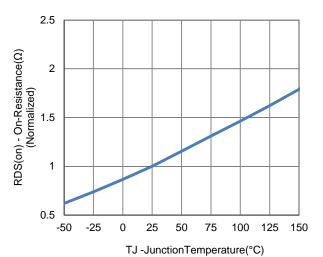
Typical Electrical Characteristics



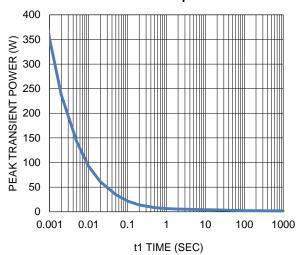
7. Gate Charge (nC)



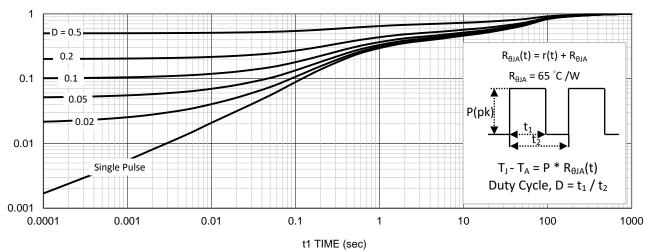
9. Safe Operating Area



8. Normalized On-Resistance Vs Junction Temperature

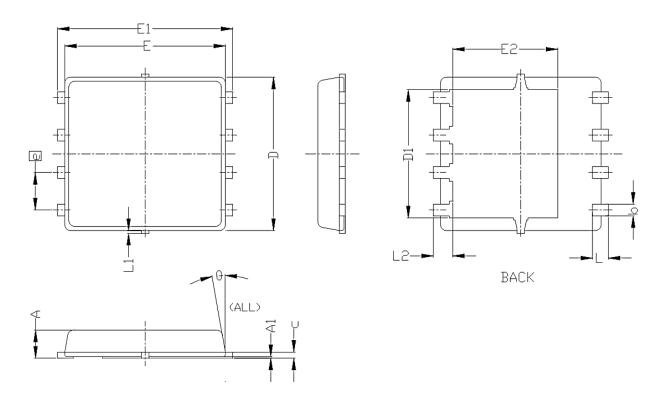


10. Single Pulse Maximum Power Dissipation



11. Normalized Thermal Transient Junction to Ambient

Package Information



SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES			
STMDOLS	MIN	NOM	MAX	MIN	NOM	MAX	
Α	0.85	0.95	1.00	0.033	0.037	0.039	
A1	0.00		0.05	0.000		0.002	
b	0.30	0.40	0.50	0.012	0.016	0.020	
с	0. 15	0.20	0. 25	0.006	0.008	0.010	
D	5. 20 BSC			0. 205 BSC			
D1	4. 35 BSC			0. 171 BSC			
Е	5, 55 BSC			0. 219 BSC			
E1	6. 05 BSC			0. 238 BSC			
E2	3. 62 BSC			0. 143 BSC			
e	1. 27 BSC			0. 050 BSC			
L	0.45	0.55	0.65	0.018	0.022	0.026	
L1	0		0.15	0		0.006	
L2	0.68 REF			0. 027 REF			
θ	0°		10°	0°		10°	